SNRI2023 Lab 1 CMOS Cryogenic Readout Electronics

Scuola Nazionale dei Rivelatori Innovativi 2023

Torino 2023-10-09



Istituto Nazionale di Fisica Nucleare

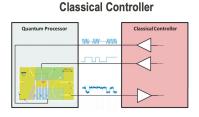
Manuel Rolo Fabio Cossio Sofia Blua

Context and Definitions



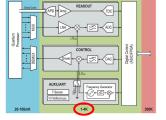
"Deep Cryogenic" electronics for Quantum technologies

- Towards the development of novel quantum sensor technologies through the consolidation and scaling up of existing and emerging technologies;
 - provide advanced enabling infrastructures and key capabilities for the development of cryogenic electronics in order to solve "the wiring bottleneck" on quantum computers;
 - cryogenic CMOS operating <4K and down to the mK pave the way for scalability into the million qubit realm.

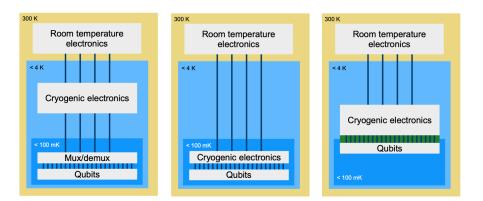


- Electronics to control and read-out the quantum processor mostly operated at room temperature (RT)
- Does not scale with the number of qubits

CMOS Integrated Controller



 More scalable approach by moving the control and read-out electronics closer to the qubits and operate it at cryogenic temperature (around 4 K)



C. Degenhardt, "Cryogenic QUBIT Control – The Tyranny of numbers, self-heating and everything"

 [□] E. Charbon, ESSCIRC 2019.
□ B. Patra, et al., JSSC, vol. 53, no. 1, 2018

Context and Definitions

"Mild cryogenic" electronics for Liquid Detectors

- Rare-event search on astroparticles: neutrino physics and direct dark matter detection using liquid scintillators e.g. Liquid Xenon (LXe) and Liquid Argon (LAr);
- Single and dual-phase detectors employing (solid-state) photon sensors require front-end readout electronics operating at 165K (LXe) or 88K (LAr).

| Type | Photon detector | Area (m^2) |
|----------------|---|--|
| LXe | SiPMs (FBK [Ch2-18], Hamamatsu [Ch2-19]), | 5 |
| | digital 3D-SiPM | |
| \mathbf{LXe} | PMTs, SiPMs or Hybrids | 8 |
| | (SIGHT, ABALONE) | |
| LSci | FBK SiPMs | 10 |
| \mathbf{LAr} | SiPMs (FBK NUV-HD triple-dopant) | 30 |
| LAr | SiPM is baseline option | 200 |
| \mathbf{LAr} | Light guide or $trap + SiPM$ | 10-1000 |
| | LXe LXe LSci LAr LAr | LXeSiPMs (FBK [Ch2-18], Hamamatsu [Ch2-19]), digital 3D-SiPMLXePMTs, SiPMs or Hybrids (SIGHT, ABALONE)LSciFBK SiPMsLArSiPMs (FBK NUV-HD triple-dopant)LArSiPM is baseline option |

Need to commit to strong R&D programs for the development and deployment of new readout schemes suitable for future large-scale neutrino and dark matter detectors;

today's solutions are not scalable.

Future larger scale experiments will call for innovative cold integrated readout electronics implementing digital signal processing within the photosensor detection module.

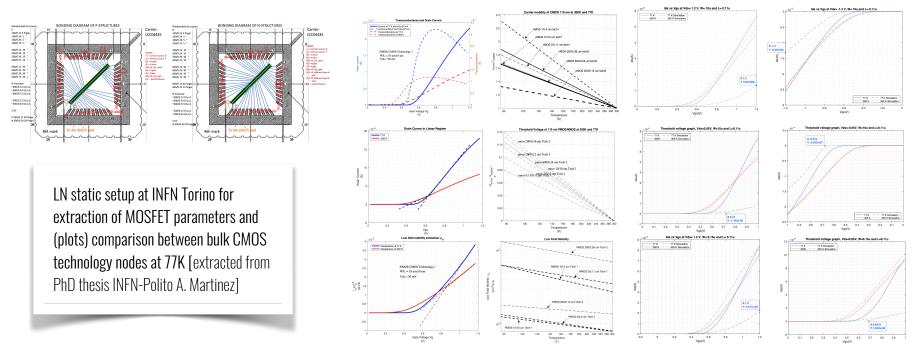
"R&D on the 5-year horizon for greater integration include (...) dedicated ASIC design; 3D-vertical integration R&D; and development of lower-power, larger-area and lower-radioactivity photodetection modules."



CMOS Cryogenic Electronics

Challenges for circuit design and operation

- CMOS Process Design Kits typically valid down to 233K (-40°C), although models scale relatively well down to 77K. This was verified with VDSM bulk and FDSOI technology nodes.
- Cold CMOS PDKs are fundamental for the development of complex mixed-signal ASICs allowing for innovative detector architecture and concepts, data transfer, readout and control.
- If no Cold PDK is available, design test structures and extract MOSFET parameters to guide the circuit design:

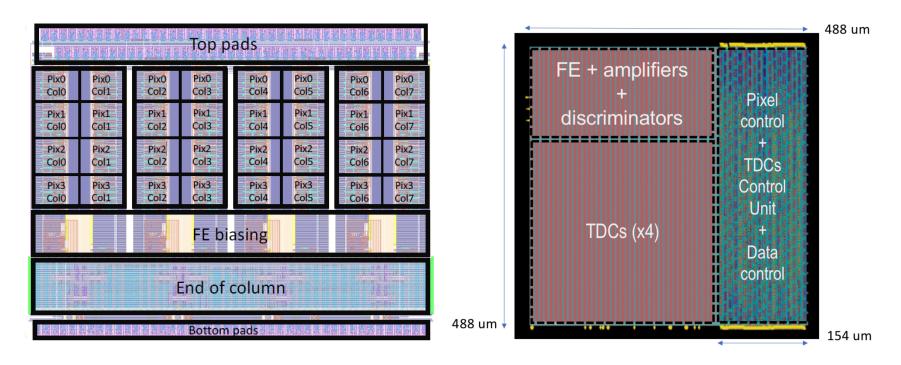




An ASIC for SiPM readout at Cryogenic Temperature

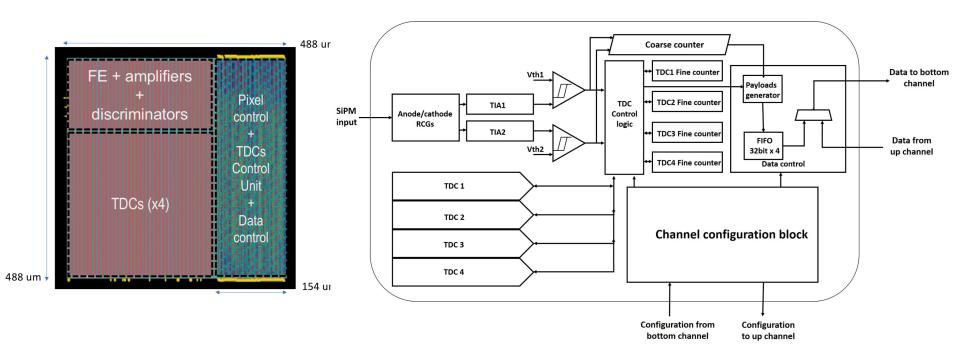


- 32-pixel matrix mixed signal ASIC (CMOS 110nm) developed by INFN, VFE optimised for **operation at 77K**
- the chip performs amplification, signal conditioning and event digitisation, and features fully digital I/O
- Single-photon time tagging mode or time and charge measurement
- 4 LVDS TX data links, SPI configuration, operation at 160/320 MHz (TDC binning 100 or 50 ps, respectively)

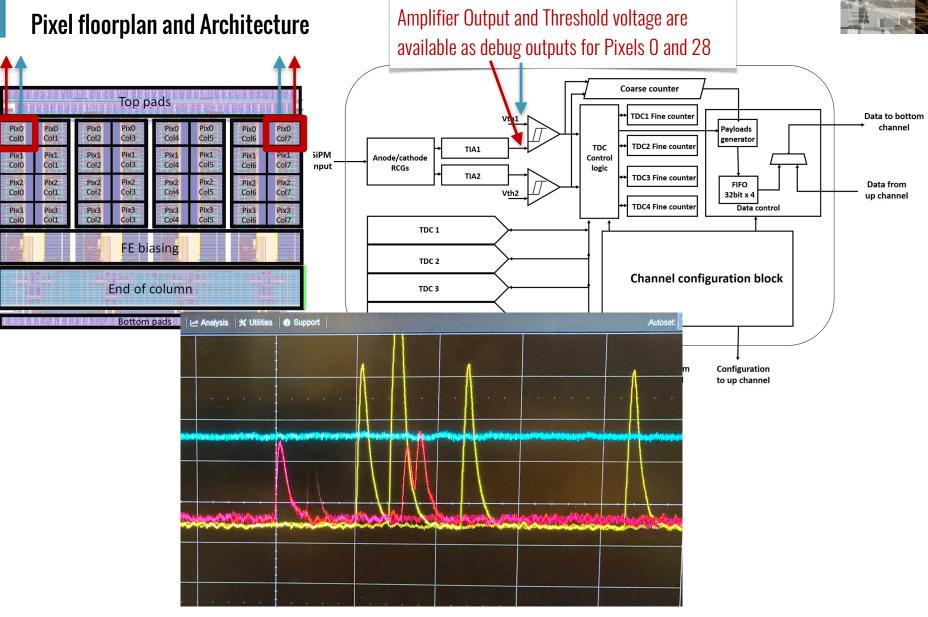




Pixel floorplan and Architecture



- dual-polarity RCG-based preamplifier: high bandwidth and low input-impedance (10-20 Ω)
- 2 independent post-amp branches and 4 gain settings
- Dual leading edge discriminators with independent (and per pixel) threshold settings (6-bit DAC)
- Pixel control logic handles quad-TDC operation, pixel configuration and data transmission

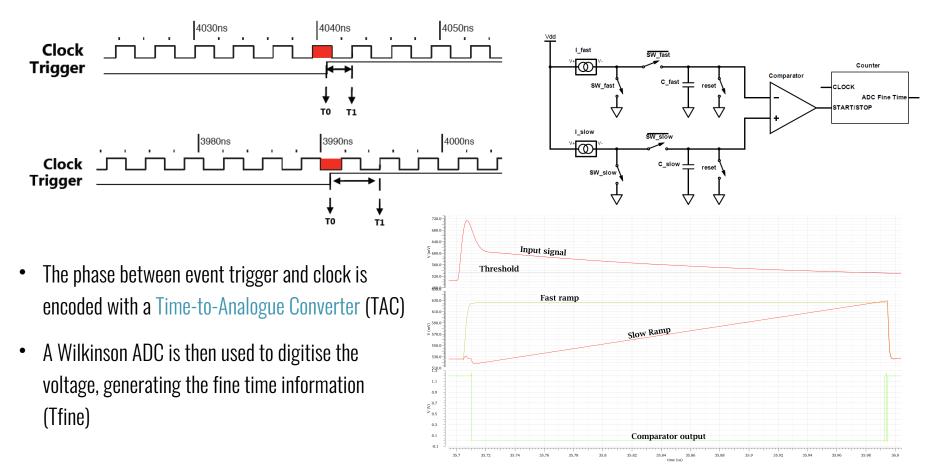


SNRI 2023

Time-to-Digital Converters

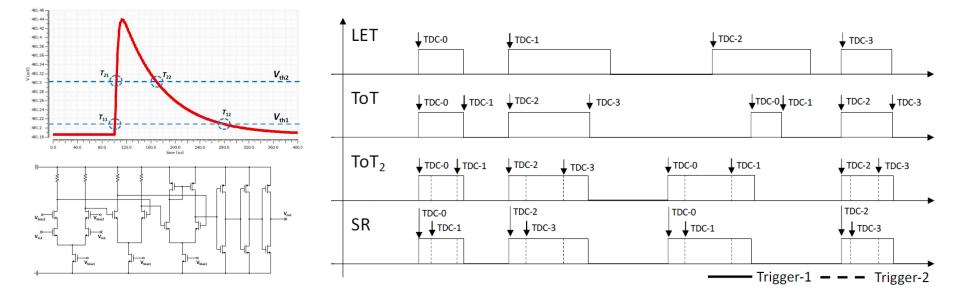
SNRI 2023

- A coarse time stamp is extracted from the system clock running up to 320 MHz
- A Low-power Analogue interpolation TDC measures phase between event trigger (TO) and clock (T1)





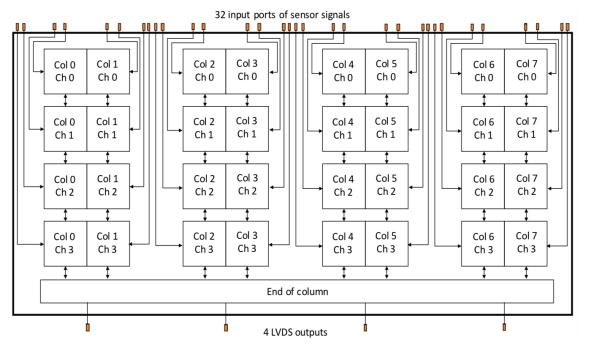
Pixel Operation Modes



- LET leading edge threshold measurement, high-rate time-stamp architecture
- **TOT** Time-over-Threshold (selectable branch for falling edge measurement)
- SR slew-rate measurement for signal shape characterisation
- Pixel can be disabled, in normal (trigger less) acquisition mode or can be triggered by a test-pulse,
 - either generated by the on-chip calibration circuitry or propagated from the DAQ,
 - either injecting a configurable charge to the front-end or triggering asynchronously the pixel logic for characterisation and calibration of the TDCs



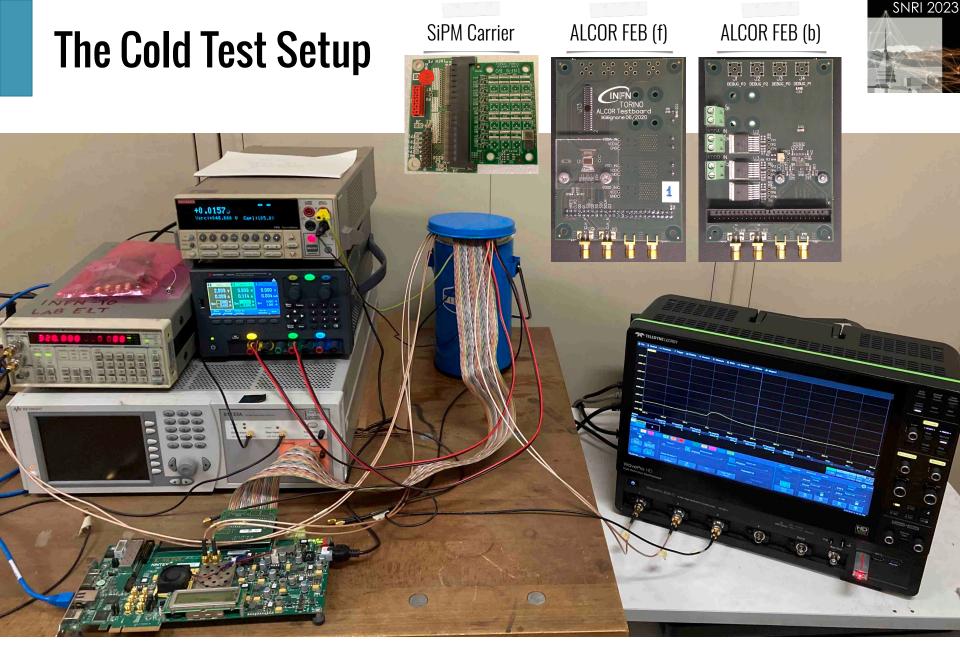
Pixel Operation Modes

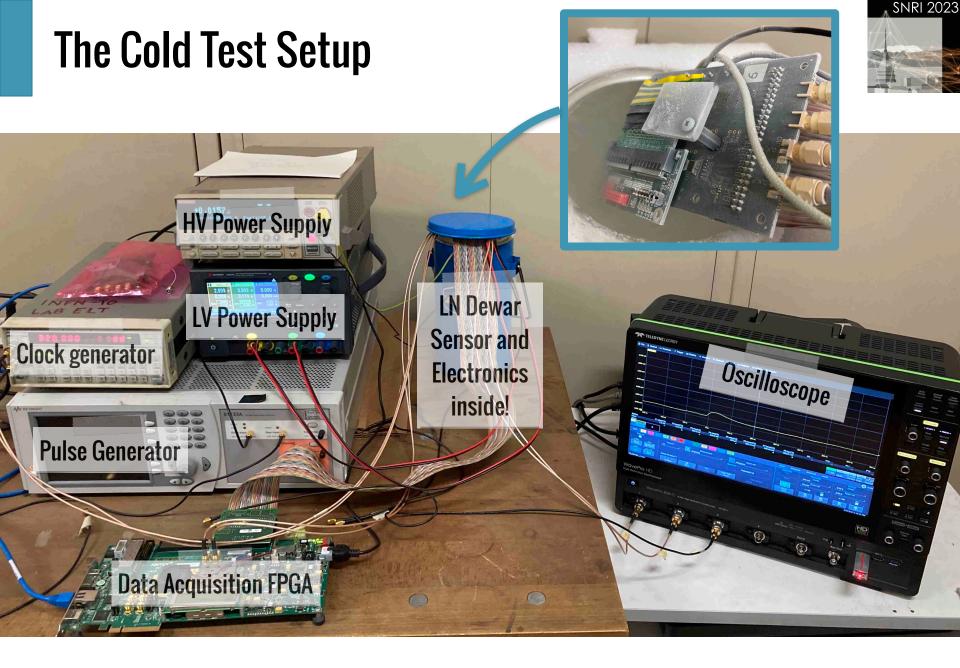


- 32-pixel matrix (4×8 array) mixed-signal ASIC
- SPI-based chip configuration

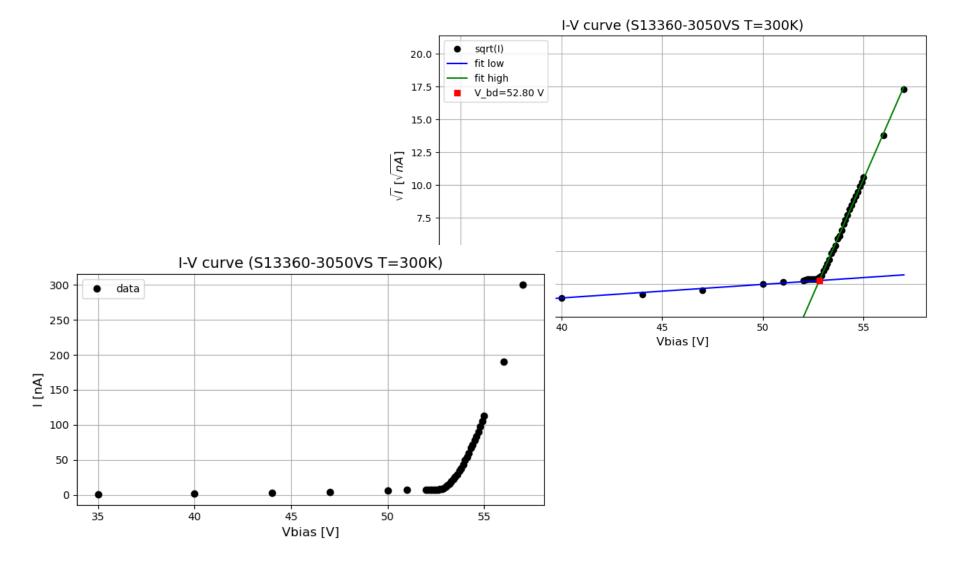
| Column ID 3 bits | | Channel ID | TDO | 2 bits | | nter Fine | Fine counter 9 bits | |
|---------------------|----------|---------------|----------------------|-----------|-----------|----------------------|------------------------|--|
| | | 3 bits | 2 b | | | 9 | | |
| Status wo | rd | | | | | | | |
| Column | Pixel ID | Lost event | Lost e.w. counter | Lost e.w. | Lost e.w. | Lost e.w. counter | SEU | |
| Column ID | | | | | | | SEU counter | |

- 64-bit (32-bit on time tagging mode) event and status data is generated on-pixel and propagated down the column
- End of Column collects digitised data from pixels and transmits it off-chip using (up to) 4 LVDS Tx links
- End of Column provides also configuration (and analogue bias) to the pixel "matrix"





SiPM: extraction of Breakdown Voltage at 300K

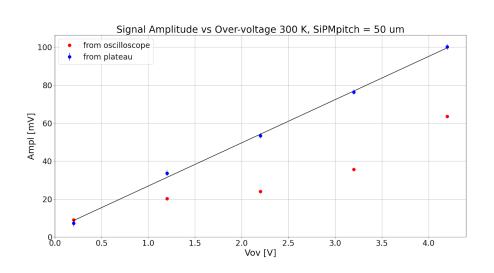


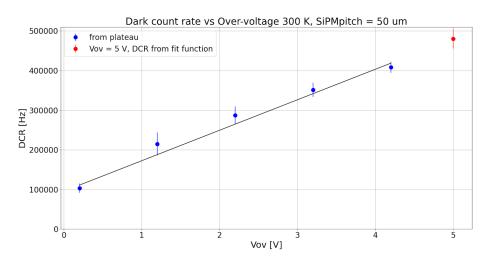
13

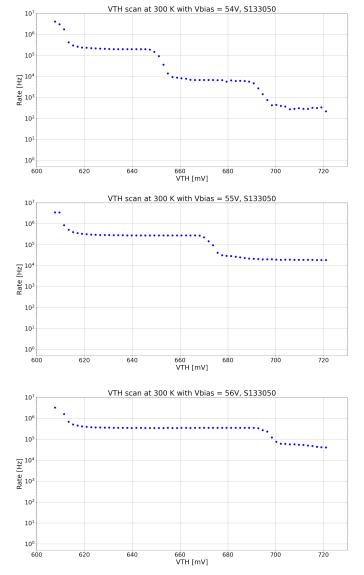


" SNRI 2023

Dark Count Rate (DCR) and signal amplitude studies at 300K



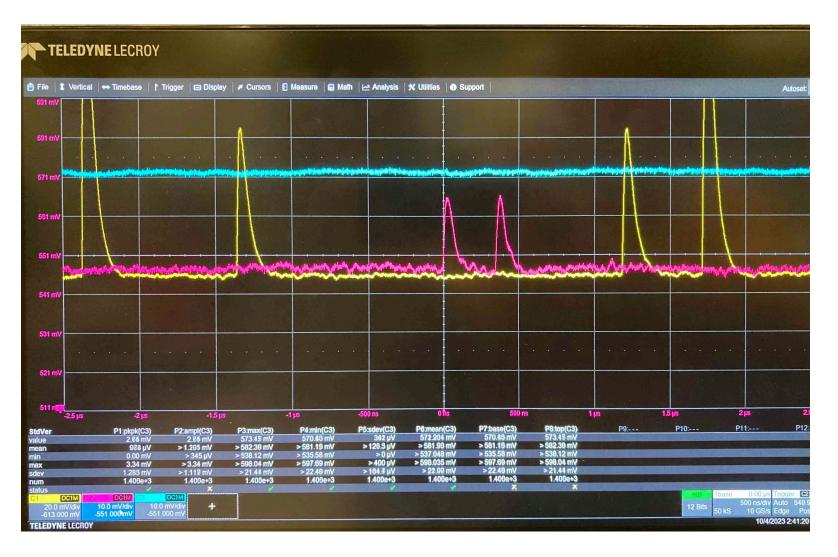




14



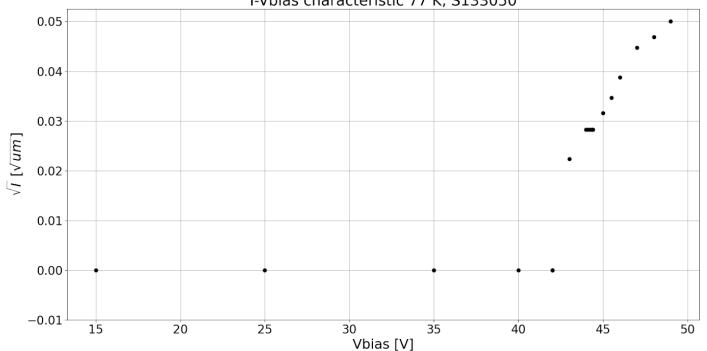
Studies of signal amplitude and threshold scans during cool-down





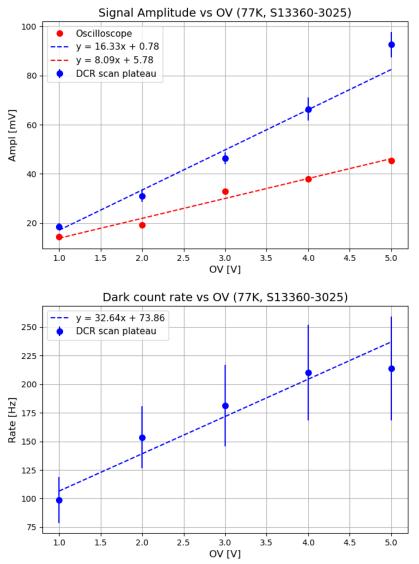
SiPM: extraction of Breakdown Voltage at 77K





I-Vbias characteristic 77 K, S133050

Dark Count Rate (DCR) and signal amplitude studies at 77K



Rate [Hz] 104 103 10² 10¹ 10⁰ VTH [mV] VTH scan at 77 K with Vbias = 46V 10^{6} Rate [Hz] 10, 10, 10¹ 10⁰ VTH [mV] VTH scan at 77 K with Vbias = 47V Rate [Hz] 10¹ 10⁰ VTH [mV]

VTH scan at 77 K with Vbias = 45V

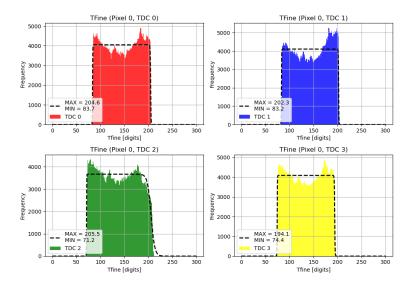


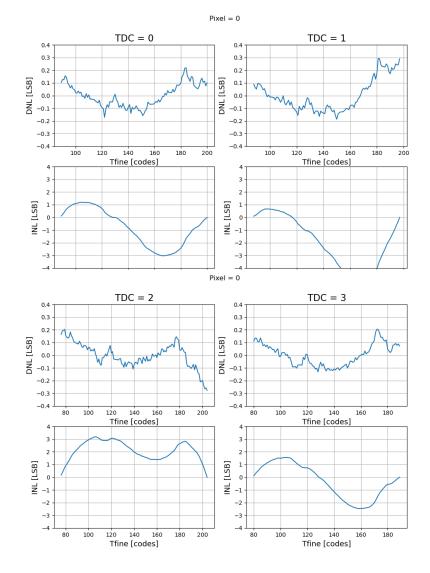
Characterisation of Time-to-Digital Converters

SNRI 2023



• Quantisation error (RT vs. LN)





The Cold Test Setup

on the definition of "Hands-On Laboratory"...

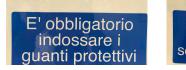
- Test setup uses Liquid Nitrogen (77K)
- Handling of the electronics and cabling during test with LN (cool-down and warm-up) will be sorted out by the Laboratory Lecturer
- Keep a safe distance from the dewar during re-fill operations













Lab Support Material

what's inside

